

TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT process)

2SA950

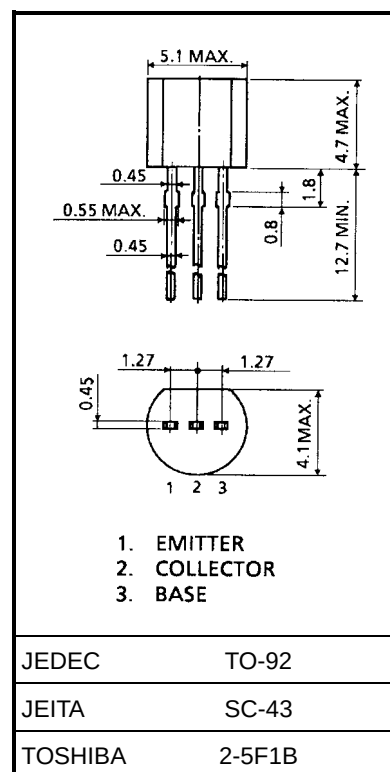
Audio Power Amplifier Applications

Unit: mm

- High h_{FE} : $h_{FE} = 100 \sim 320$
- 1 W output applications
- Complementary to 2SC2120

Maximum Ratings ($T_a = 25^\circ\text{C}$)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-35	V
Collector-emitter voltage	V_{CEO}	-30	V
Emitter-base voltage	V_{EBO}	-5	V
Collector current	I_C	-800	mA
Base current	I_B	-160	mA
Collector power dissipation	P_C	600	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature range	T_{stg}	-55~150	$^\circ\text{C}$



Weight: 0.21 g (typ.)

Electrical Characteristics ($T_a = 25^\circ\text{C}$)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	I_{CBO}	$V_{CB} = -35\text{ V}, I_E = 0$	—	—	-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5\text{ V}, I_C = 0$	—	—	-0.1	μA
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -10\text{ mA}, I_B = 0$	-30	—	—	V
DC current gain	$h_{FE(1)}$ (Note)	$V_{CE} = -1\text{ V}, I_C = -100\text{ mA}$	100	—	320	
	$h_{FE(2)}$	$V_{CE} = -1\text{ V}, I_C = -700\text{ mA}$	35	—	—	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -500\text{ mA}, I_B = -20\text{ mA}$	—	—	-0.7	V
Base-emitter voltage	V_{BE}	$V_{CE} = -1\text{ V}, I_C = -10\text{ mA}$	-0.5	—	-0.8	V
Transition frequency	f_T	$V_{CE} = -5\text{ V}, I_C = -10\text{ mA}$	—	120	—	MHz
Collector output capacitance	C_{ob}	$V_{CB} = -10\text{ V}, I_E = 0, f = 1\text{ MHz}$	—	19	—	pF

Note: h_{FE} (1) classification O: 100~200, Y: 160~320

